

# MUN2230, MMUN2230L, MUN5230, DTC113EE, DTC113EM3, NSBC113EF3

## Digital Transistors (BRT) R1 = 1 kΩ, R2 = 1 kΩ

### NPN Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current - Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	10	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	10	Vdc

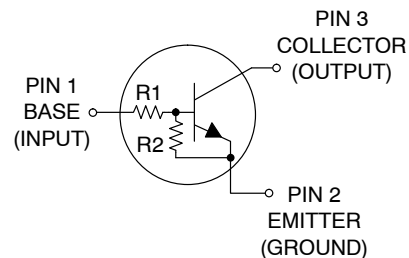
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



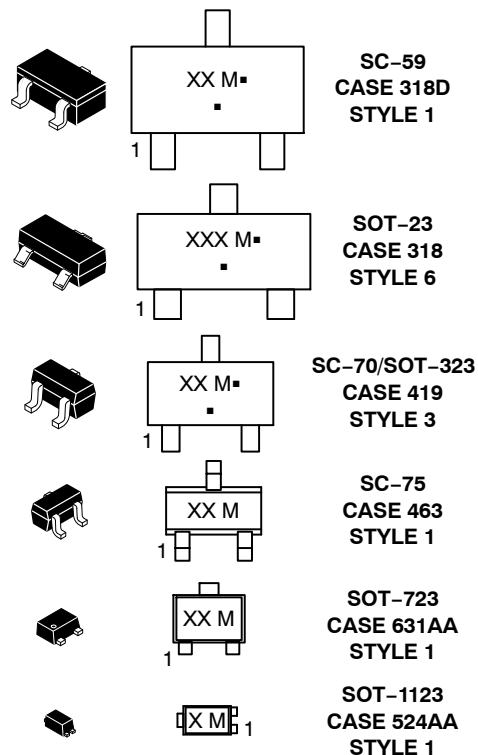
ON Semiconductor®

<http://onsemi.com>

#### PIN CONNECTIONS



#### MARKING DIAGRAMS



XXX = Specific Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

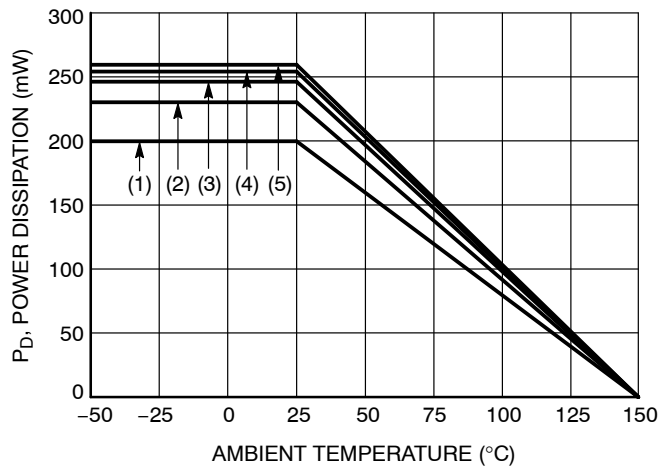
# MUN2230, MMUN2230L, MUN5230, DTC113EE, DTC113EM3, NSBC113EF3

**Table 1. ORDERING INFORMATION**

Device	Part Marking	Package	Shipping†
MUN2230T1G, SMUN2230T1G	8G	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2230LT1G	A8G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5230T1G	8G	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTC113EET1G	7Q	SC-75 (Pb-Free)	3000 / Tape & Reel
DTC113EM3T5G	7A	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBC113EF3T5G	D (180°)*	SOT-1123 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\* (xx°) = Degree rotation in the clockwise direction.



- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
- (5) SOT-723; Minimum Pad

**Figure 1. Derating Curve**

**MUN2230, MMUN2230L, MUN5230, DTC113EE, DTC113EM3, NSBC113EF3**

**Table 2. THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
<b>THERMAL CHARACTERISTICS (SC-59) (MUN2230)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	(Note 1) (Note 2) (Note 1) (Note 2)	$P_D$ 230 338 1.8 2.7	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$ 540 370	$^\circ\text{C/W}$
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{\theta JL}$ 264 287	$^\circ\text{C/W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
<b>THERMAL CHARACTERISTICS (SOT-23) (MMUN2230L)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	(Note 1) (Note 2) (Note 1) (Note 2)	$P_D$ 246 400 2.0 3.2	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$ 508 311	$^\circ\text{C/W}$
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{\theta JL}$ 174 208	$^\circ\text{C/W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
<b>THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5230)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	(Note 1) (Note 2) (Note 1) (Note 2)	$P_D$ 202 310 1.6 2.5	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$ 618 403	$^\circ\text{C/W}$
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{\theta JL}$ 280 332	$^\circ\text{C/W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
<b>THERMAL CHARACTERISTICS (SC-75) (DTC113EE)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	(Note 1) (Note 2) (Note 1) (Note 2)	$P_D$ 200 300 1.6 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$ 600 400	$^\circ\text{C/W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
<b>THERMAL CHARACTERISTICS (SOT-723) (DTC113EM3)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	(Note 1) (Note 2) (Note 1) (Note 2)	$P_D$ 260 600 2.0 4.8	mW mW/ $^\circ\text{C}$

1. FR-4 @ Minimum Pad.
2. FR-4 @ 1.0 x 1.0 Inch Pad.
3. FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
4. FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

MUN2230, MMUN2230L, MUN5230, DTC113EE, DTC113EM3, NSBC113EF3

Table 2. THERMAL CHARACTERISTICS

Characteristic		Symbol	Max	Unit
<b>THERMAL CHARACTERISTICS (SOT-723) (DTC113EM3)</b>				
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	480 205	$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to +150	$^{\circ}\text{C}$
<b>THERMAL CHARACTERISTICS (SOT-1123) (NSBC113EF3)</b>				
Total Device Dissipation $T_A = 25^{\circ}\text{C}$	(Note 3) (Note 4)	$P_D$	254 297	mW
Derate above $25^{\circ}\text{C}$	(Note 3) (Note 4)		2.0 2.4	$\text{mW}/^{\circ}\text{C}$
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4)	$R_{\theta JA}$	493 421	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction to Lead	(Note 3)	$R_{\theta JL}$	193	$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to +150	$^{\circ}\text{C}$

1. FR-4 @ Minimum Pad.
2. FR-4 @ 1.0 x 1.0 Inch Pad.
3. FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
4. FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

# MUN2230, MMUN2230L, MUN5230, DTC113EE, DTC113EM3, NSBC113EF3

**Table 3. ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector–Base Cutoff Current ( $V_{CB} = 50\text{ V}$ , $I_E = 0$ )	$I_{CBO}$	–	–	100	nAdc
Collector–Emitter Cutoff Current ( $V_{CE} = 50\text{ V}$ , $I_B = 0$ )	$I_{CEO}$	–	–	500	nAdc
Emitter–Base Cutoff Current ( $V_{EB} = 6.0\text{ V}$ , $I_C = 0$ )	$I_{EBO}$	–	–	4.3	mAdc
Collector–Base Breakdown Voltage ( $I_C = 10\ \mu\text{A}$ , $I_E = 0$ )	$V_{(BR)CBO}$	50	–	–	Vdc
Collector–Emitter Breakdown Voltage (Note 5) ( $I_C = 2.0\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	50	–	–	Vdc
<b>ON CHARACTERISTICS</b>					
DC Current Gain (Note 5) ( $I_C = 5.0\text{ mA}$ , $V_{CE} = 10\text{ V}$ )	$h_{FE}$	3.0	5.0	–	
Collector–Emitter Saturation Voltage (Note 5) ( $I_C = 10\text{ mA}$ , $I_B = 5.0\text{ mA}$ )	$V_{CE(sat)}$	–	–	0.25	Vdc
Input Voltage (off) ( $V_{CE} = 5.0\text{ V}$ , $I_C = 100\ \mu\text{A}$ )	$V_{i(off)}$	–	1.2	0.5	Vdc
Input Voltage (on) ( $V_{CE} = 0.3\text{ V}$ , $I_C = 20\text{ mA}$ )	$V_{i(on)}$	2	1.6	–	Vdc
Output Voltage (on) ( $V_{CC} = 5.0\text{ V}$ , $V_B = 2.5\text{ V}$ , $R_L = 1.0\text{ k}\Omega$ )	$V_{OL}$	–	–	0.2	Vdc
Output Voltage (off) ( $V_{CC} = 5.0\text{ V}$ , $V_B = 0.05\text{ V}$ , $R_L = 1.0\text{ k}\Omega$ )	$V_{OH}$	4.9	–	–	Vdc
Input Resistor	$R_1$	0.7	1.0	1.3	$\text{k}\Omega$
Resistor Ratio	$R_1/R_2$	0.8	1.0	1.2	

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle  $\leq$  2%.

TYPICAL CHARACTERISTICS  
 MUN2230, MMUN2230L, MUN5230, DTC113EE, DTC113EM3, NSBC113EF3

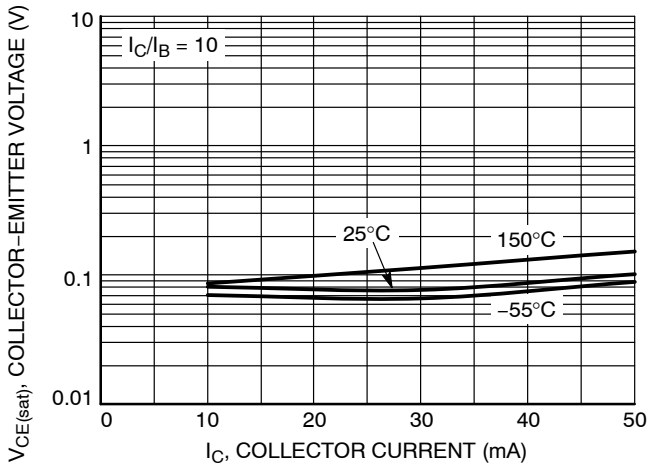


Figure 2.  $V_{CE(sat)}$  vs.  $I_C$

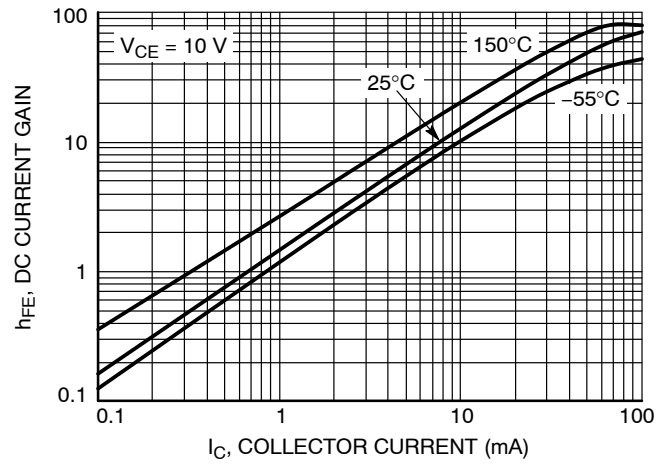


Figure 3. DC Current Gain

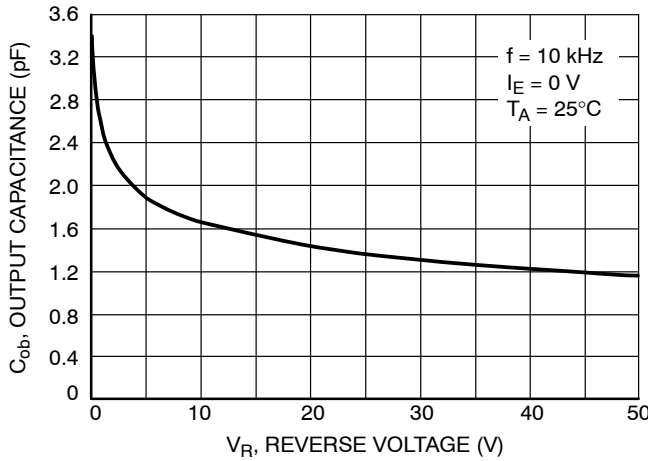


Figure 4. Output Capacitance

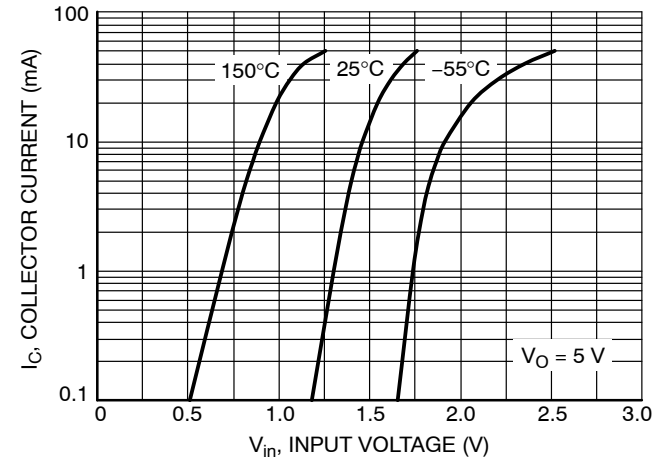


Figure 5. Output Current vs. Input Voltage

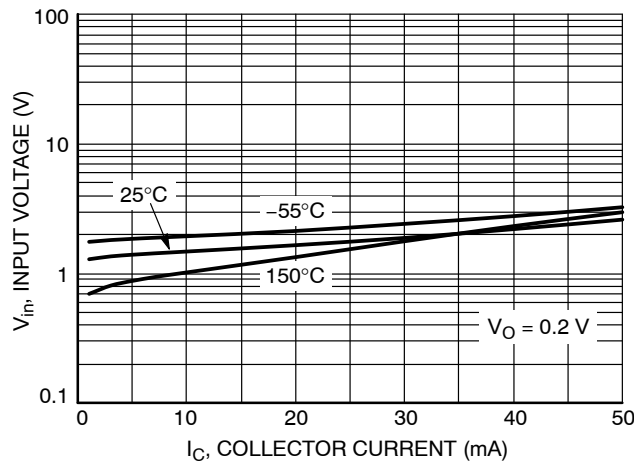


Figure 6. Input Voltage vs. Output Current

PACKAGE DIMENSIONS

SC-59  
CASE 318D-04  
ISSUE H



- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
c	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118

- STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AP

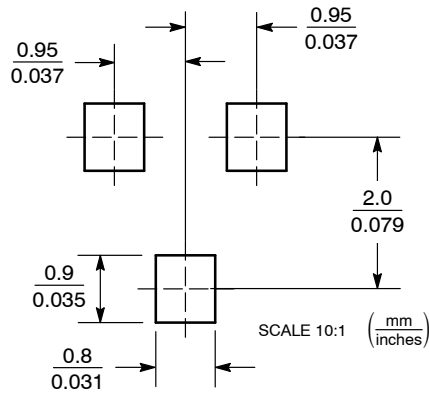


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

STYLE 6:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

SOLDERING FOOTPRINT





PACKAGE DIMENSIONS

SC-70 (SOT-323)  
CASE 419-04  
ISSUE N



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 3:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SC-75/SOT-416  
CASE 463  
ISSUE F



- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
C	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.059	0.063	0.067
E	0.70	0.80	0.90	0.027	0.031	0.035
e	1.00 BSC			0.04 BSC		
L	0.10	0.15	0.20	0.004	0.006	0.008
HE	1.50	1.60	1.70	0.061	0.063	0.065

- STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

SOLDERING FOOTPRINT\*

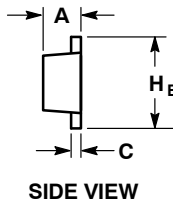


SCALE 10:1 ( $\frac{\text{mm}}{\text{inches}}$ )

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-723  
CASE 631AA-01  
ISSUE D



NOTES:

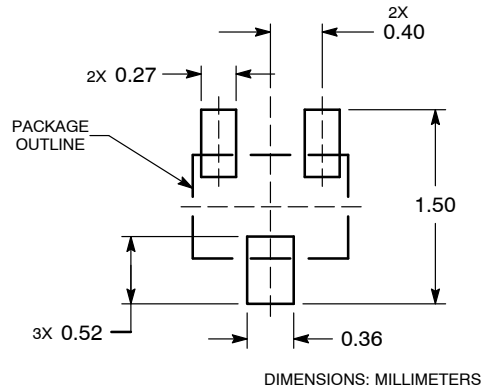
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H E	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

STYLE 1:

1. BASE
2. EMITTER
3. COLLECTOR

RECOMMENDED  
SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

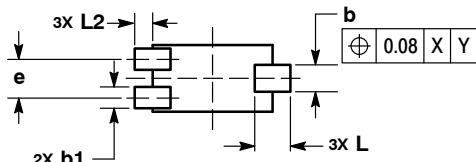
SOT-1123  
CASE 524AA  
ISSUE C



TOP VIEW



SIDE VIEW



BOTTOM VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.34	0.40
b	0.15	0.28
b1	0.10	0.20
c	0.07	0.17
D	0.75	0.85
E	0.55	0.65
e	0.35	0.40
HE	0.95	1.05
L	0.185	REF
L2	0.05	0.15

STYLE 1:

1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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